

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
26 May 2005 (26.05.2005)

PCT

(10) International Publication Number
WO 2005/048351 A1

(51) International Patent Classification⁷: **H01L 29/10**,
29/739, 21/331

(21) International Application Number:
PCT/CH2004/000691

(22) International Filing Date:
16 November 2004 (16.11.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
03405816.4 17 November 2003 (17.11.2003) EP

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

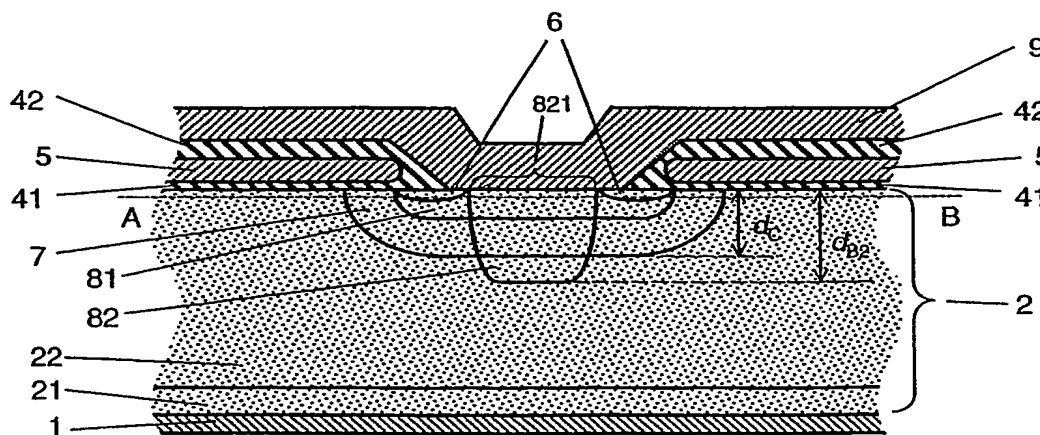
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE,
SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

Published:

- with international search report
- with amended claims

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: IGBT CATHODE DESIGN WITH IMPROVED SAFE OPERATING AREA CAPABILITY



(57) Abstract: In an insulated gate bipolar transistor, an improved safe operating area capability is achieved according to the inven-
tion by a two-fold base region comprising a first base region (81), which is disposed in the channel region (7) so that it encompasses
the one or more source regions (6), but does not adjoin the second main surface underneath the gate oxide layer (41), and a second
base region (82) is disposed in the semiconductor substrate (2) underneath the base contact area (821) so that it partially overlaps
with the channel region (7) and with the first base region (81).

WO 2005/048351 A1